CST20L40CT

20A Trench Low Barrier Diode

■ Features

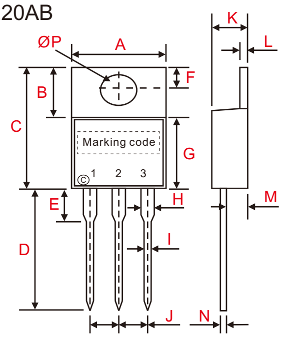
- Low forward voltage drop.
- Excellent high temperature stability.
- Fast switching capability.
- Lead-free parts meet environmental standards of MIL-STD-19500 /228

■ Mechanical data

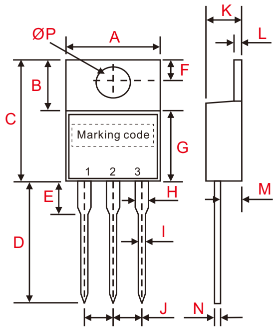
- Epoxy : UL94-V0 rated flame retardant.
- Case : JEDEC TO-220AB molded plastic body.
- Terminals : Solder plated, solderable per MIL-STD-750, Method 2026.
- Polarity: As marked.
- Mounting Position : Any.
- Weight : Approximated 2.25 gram.

■ Outline

TO-220AB

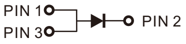


symbol	Dimensions in inches(millimeters)	
	Min	Max
A	0.398(10.1)	0.406(10.3)
B	0.236(6.0)	0.252(6.4)
C	0.579(14.7)	0.594(15.1)
D	0.543(13.8)	0.551(14.0)
E	0.143(3.63)	0.159(4.03)
F	0.104(2.64)	0.112(2.84)
G	0.335(8.5)	0.350(8.9)
H	0.046(1.17)	0.054(1.37)
I	0.028(0.71)	0.036(0.91)
J	0.098(2.49)	0.102(2.59)
K	0.176(4.47)	0.184(4.67)
L	0.046(1.17)	0.054(1.37)
M	0.102(2.6)	0.110(2.8)
N	0.019(0.28)	0.021(0.48)
ØP	0.147(3.74)	0.155(3.94)



Alternate

symbol	Dimensions in inches(millimeters)	
	Min	Max
A	0.394(10.0)	0.413(10.5)
B	0.228(5.8)	0.268(6.8)
C	0.570(14.48)	0.625(15.87)
D	0.519(13.18)	0.558(14.18)
E	0.089(3.5)	0.099(3.9)
F	0.100(2.54)	0.120(3.04)
G	0.330(8.38)	0.350(8.9)
H	0.045(1.15)	0.060(1.52)
I	0.029(0.75)	0.037(0.95)
J	0.095(2.42)	0.105(2.66)
K	0.160(4.07)	0.190(4.82)
L	0.045(1.15)	0.055(1.39)
M	0.080(2.04)	0.110(2.8)
N	0.013(0.33)	0.019(0.52)
ØP	0.148(3.75)	0.156(3.95)



■ Maximum ratings and electrical characteristics

Rating at 25°C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

Parameter	Conditions	Symbol	CST20L40CT	UNIT
Marking code			CST20L40CT	
Peak repetitive reverse voltage		V_{RRM}	40	V
Working peak reverse voltage		V_{RWM}		
DC blocking voltage		V_{RM}		
Forward rectified current (total device)		I_O	20	A
Forward surge current (per diode)	8.3ms single half sine-wave superimposed on rate load (JEDEC method)	I_{FSM}	180	A
Peak repetitive reverse surge current (per diode)	2us - 1kHz	I_{RRM}	3	A
Thermal resistance(1) (per diode)	Junction to case	$R_{\theta JC}$	2	°C/W
Operating and Storage temperature		T_J, T_{STG}	-65 ~ +150	°C

Parameter	Conditions	Symbol	MIN.	TYP.	MAX.	UNIT
Forward voltage drop (per diode)	$I_F = 10A$, $T_J = 25^{o}C$	V_F			500	mV
	$I_F = 10A$, $T_J = 125^{o}C$			410	470	
	$I_F = 20A$, $T_J = 25^{o}C$				600	
Reverse current (per diode)	$V_R = V_{RRM}$ $T_J = 25^{o}C$	I_R			0.5	mA
	$V_R = V_{RRM}$ $T_J = 125^{o}C$				100	

Note : 1.Thermal resistance from junction to case per leg, with heatsink size(1.35" x 0.95" x 0.18") Al-plate.

■ Rating and characteristic curves

Fig. 1 - Instantaneous Forward Characteristics (per diode)

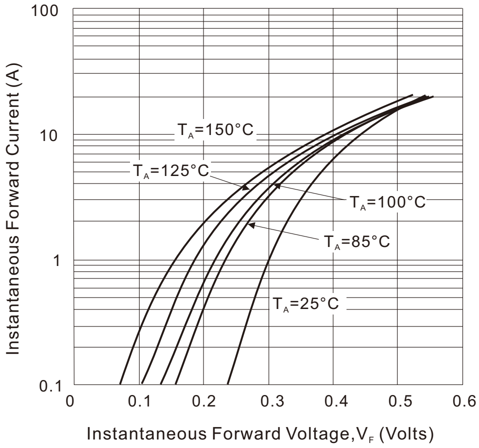


Fig.2 - Forward Current Derating Curve (per diode)

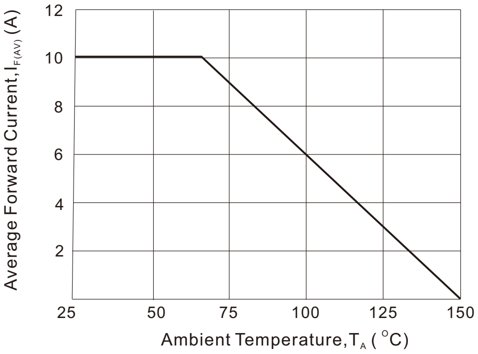


Fig. 3 - Reverse Characteristics (per diode)